

## Desirable Characteristics of Optical Sources

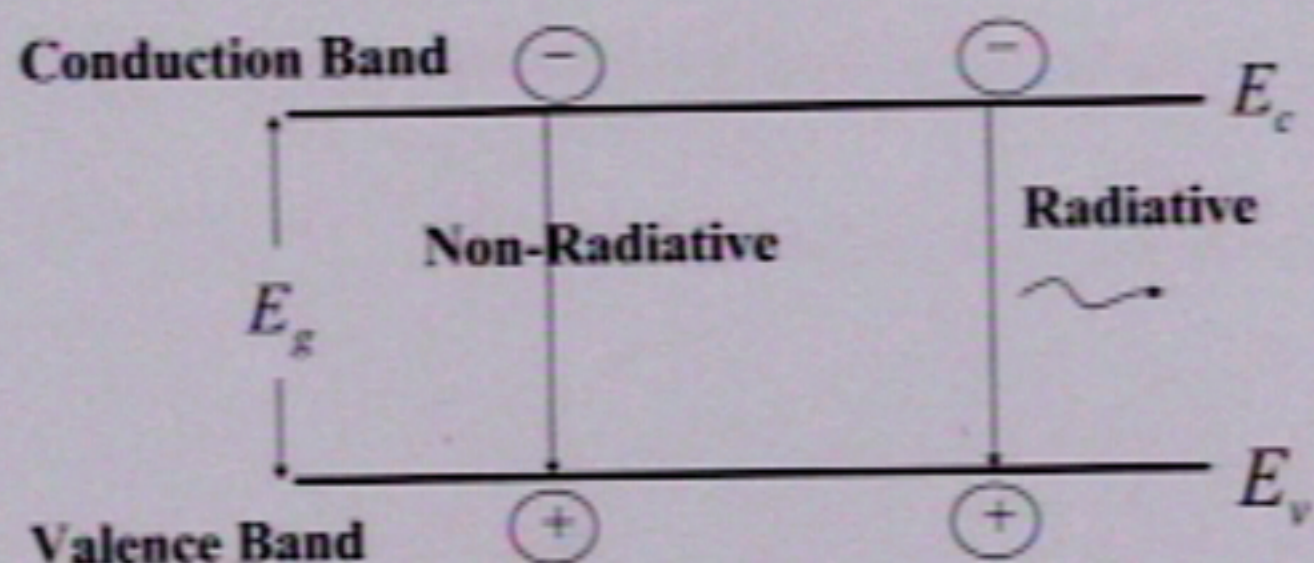
- Emission within low loss window of the fiber
- Narrow spectral width
- Capability to couple adequate power to fiber
- Ease of coupling to fiber
- Ease and linearity of modulation
- High modulation speed
- High reliability
- Ruggedness for field use



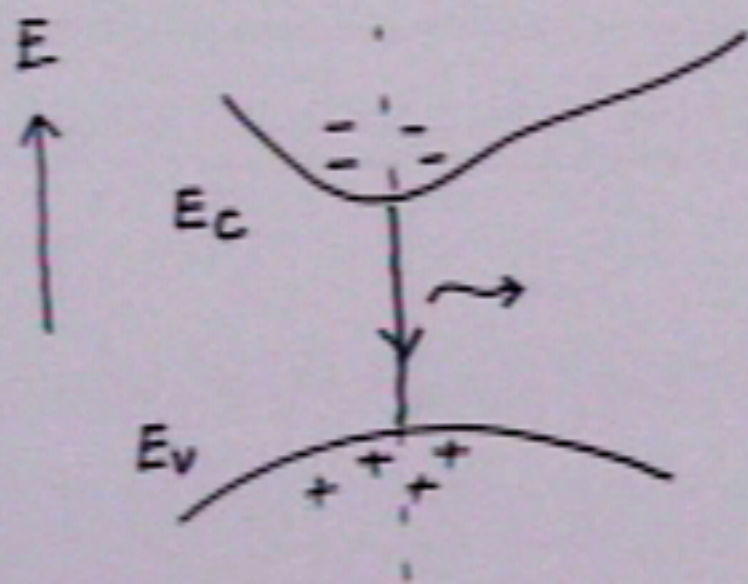
## Various Optical Sources

- Gas Sources (Lasers)
  - High power
  - Narrow spectral width
  - Highly directional
- Semiconductor Sources (Light Emitting Diode (LED), Injection Laser Diode (ILD))
  - Low power
  - Large spectral width
  - Non-directional radiation

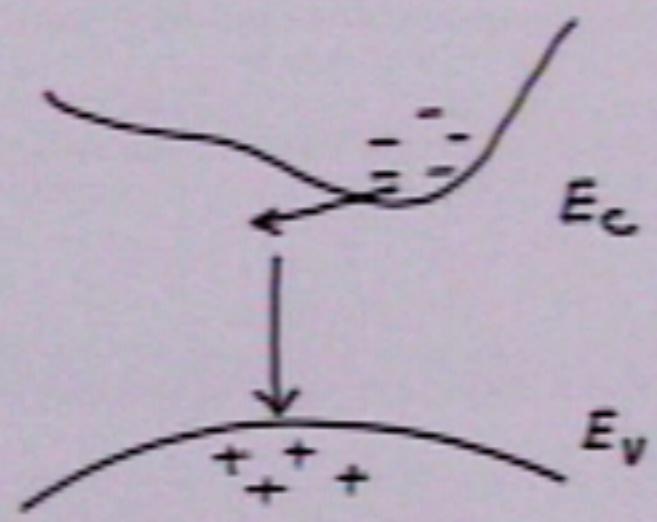
# Photon Wavelength







Direct band  
GaAs



Indirect band  
Si, Ge

→ Momentum

# Optical Sources

Direct Band gap Material

$E_2$

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$$E = E_2 - E_1 = h\nu = \frac{hc}{\lambda}$$

$$\lambda (\mu\text{m}) = \frac{1.24}{E (\text{eV})}$$

$E_1$

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For GaAs  $E = 1.4 \text{ eV}$

$$\Rightarrow \lambda = 0.8 \mu\text{m}$$

For  $\text{Ga}_x \text{Al}_{1-x} \text{As}$   $E (\text{eV}) = 1.424 + 1.266x + 0.266x^2$   $0 < x < 0.37$

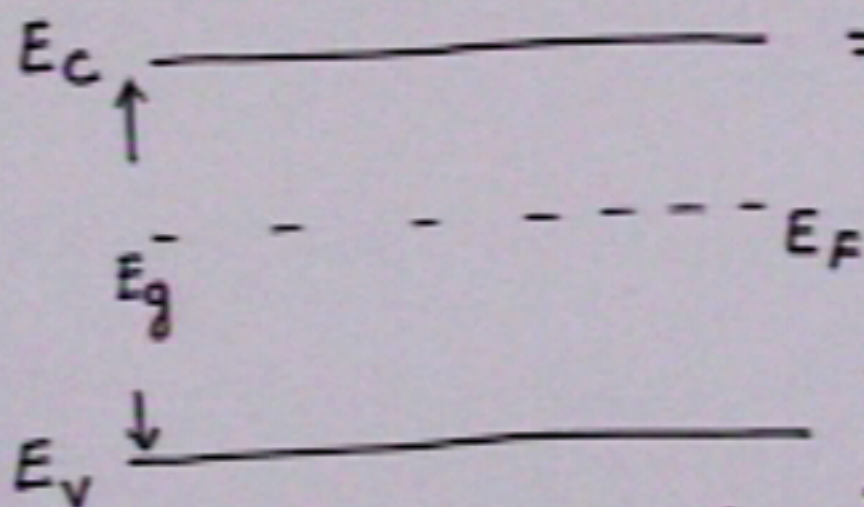
For  $\text{In}_{1-x} \text{Ga}_x \text{As}_y \text{P}_{1-y}$   $E (\text{eV}) = 1.35 - 0.72y + 0.12y^2$   $y = 2.2x$ ,  $0 < x < 0.47$

$$\Rightarrow \lambda = 0.92 - 1.65 \mu\text{m}$$



$S_C(E_2) =$  Distribution of energy states in conduction band

$$S_C(E_2) = \frac{4\pi (2m_e)^{3/2}}{h^2} (E_2 - E_C)^{1/2}$$

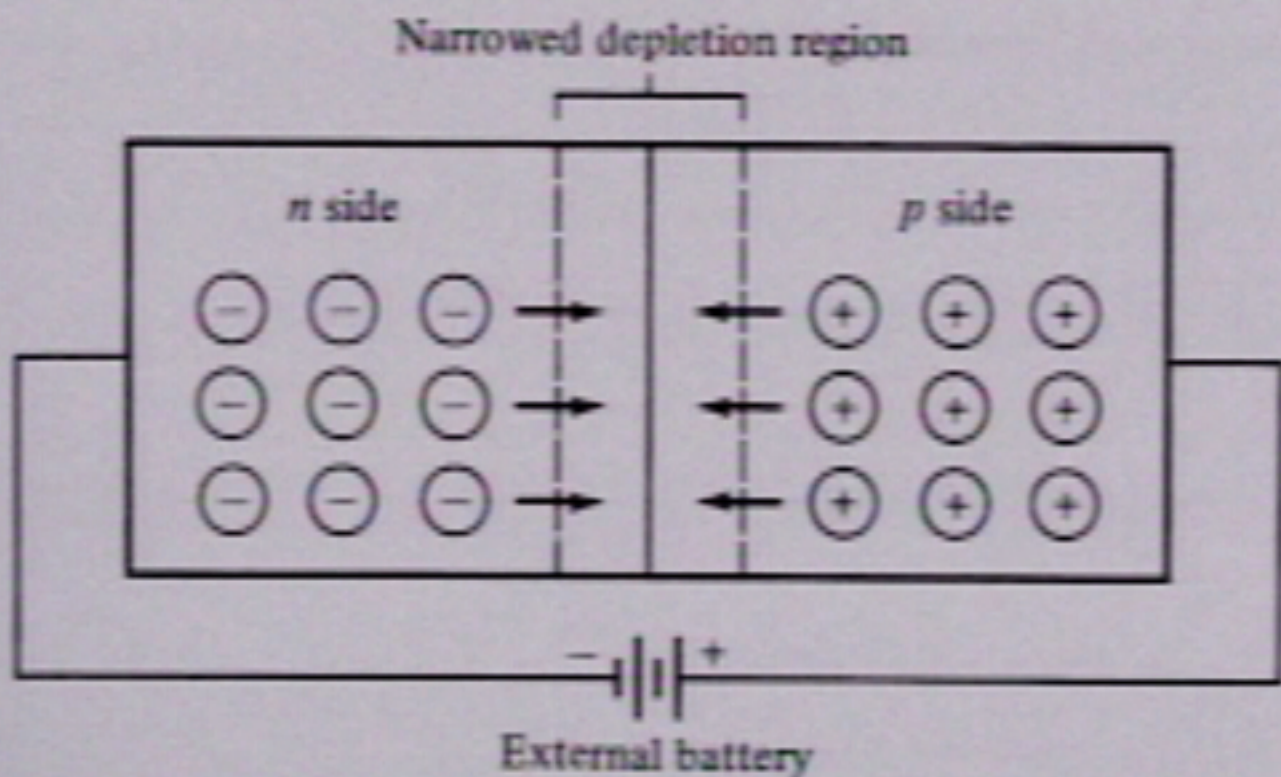


$S_V(E_1) =$  Distribution of energy states in valence band.

$$S_V(E_1) = \frac{4\pi (2m_h)^{3/2}}{h^2} (E_V - E_1)^{1/2}$$

$$F(E) = \frac{1}{1 + e^{(E - E_F)/kT}}$$

## Forward bias condition





n-type material

$$F(E_2) = \frac{E_{F_n}}{1 + e^{(E_2 - E_{F_n})/kT}}$$

$E_c$  —————  $E_{F_n}$   $\approx \frac{1}{e^{(E_2 - E_{F_n})/kT}}$

$E_v$  —————  $\approx e^{-(E_2 - E_{F_n})/kT}$

Prob of electron in conduction band

$$n(E_2) \approx e^{-(E_2 - E_{F_n})/kT}$$



p-type material

$$F(E_1) = \frac{1}{1 + e^{(E_1 - E_{Fp})/KT}}$$

Prob of absence of electron in the valence band is

$$1 - F(E_1) = 1 - \frac{1}{1 + e^{(E_1 - E_{Fp})/KT}}$$

$$E_c \text{ ————— } = 1 - \left\{ 1 + e^{(E_1 - E_{Fp})/KT} \right\}^{-1}$$

$$E_v \text{ ————— } \approx 1 - 1 + e^{(E_1 - E_{Fp})/KT}$$

Prob. of hole  $p(E_1) \approx e^{(E_1 - E_{Fp})/KT}$

Prob. of photon generation

$$\propto n(E_2) \times p(E_1)$$

$$\propto e^{-\frac{(E_2 - E_{Fn})}{kT}} \cdot e^{-\frac{(E_1 - E_{Fp})}{kT}}$$

$$\propto e^{-\frac{(E_2 - E_1)}{kT}} \cdot e^{\frac{(E_{Fn} - E_{Fp})}{kT}}$$

$$\propto e^{-\frac{(E_2 - E_1)}{kT}} \quad A - \text{const}$$